

# MM27C010

## 131,072 x 8 CMOS EPROM

### PRELIMINARY INFORMATION

#### FEATURES

- Fast read access time: 90 ns
- JEDEC-approved pinout
- High-speed write programming
  - Typically less than 16 seconds
- 5V  $\pm$ 10% power supply tolerance available
- Both CMOS and TTL compatible input and output
- Two line control functions
- Industrial and commercial temperature ranges available

#### DESCRIPTION

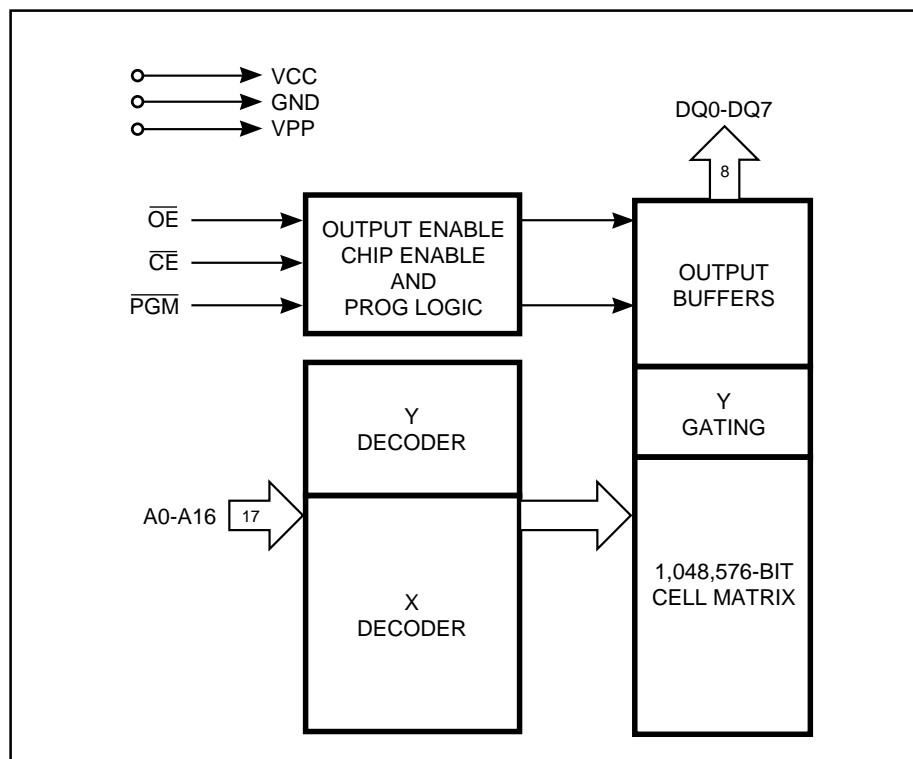
The MM27C010 is a 1 megabit (128K-word by 8-bit) CMOS Programmable Read-Only Memory. It requires only a single 5V power supply in normal read mode operation. Any byte can be accessed in less than 90 ns. The MM27C010 offers separate Output Enable ( $\overline{OE}$ ) and Chip Enable ( $\overline{CE}$ ) controls, thus eliminating bus contention in a multiple bus microprocessor system.

All signals are TTL levels, including programming signals. Bit locations may be programmed singly, in blocks, or at random.

The MM27C010 uses write programming algorithm. Programming time is typically only 100  $\mu$ s per byte.

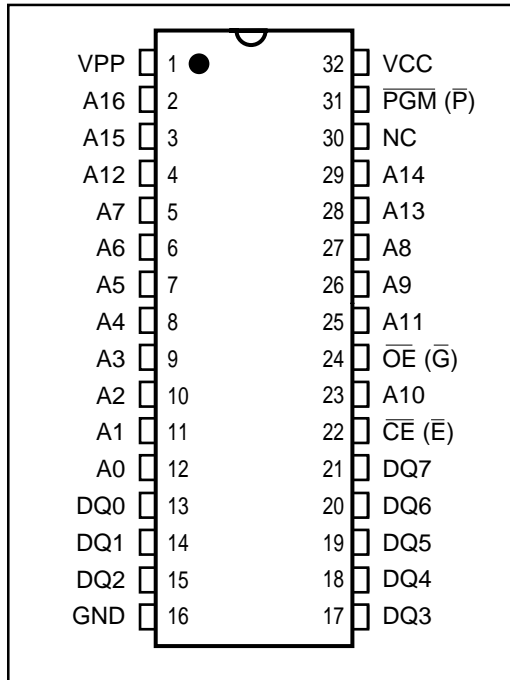
This product is available in One-Time Programmable (OTP) PDIP, PLCC, and TSOP packages over commercial and industrial temperature ranges.

#### FUNCTIONAL BLOCK DIAGRAM



**PIN CONFIGURATIONS**

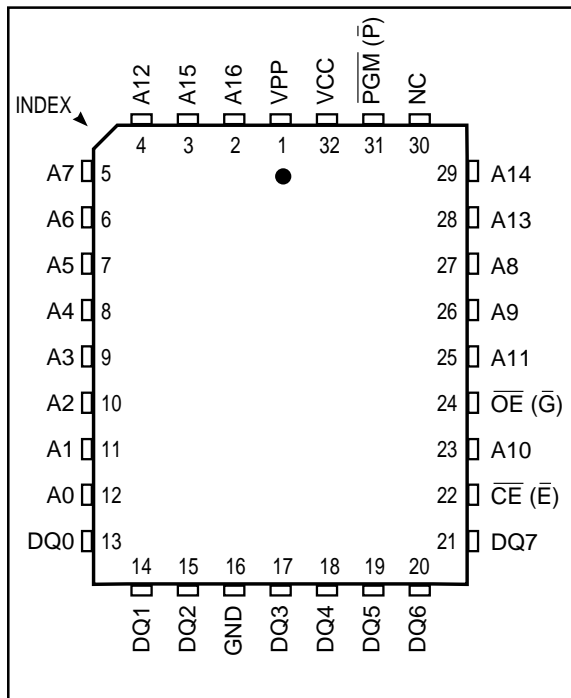
**32-Pin DIP**



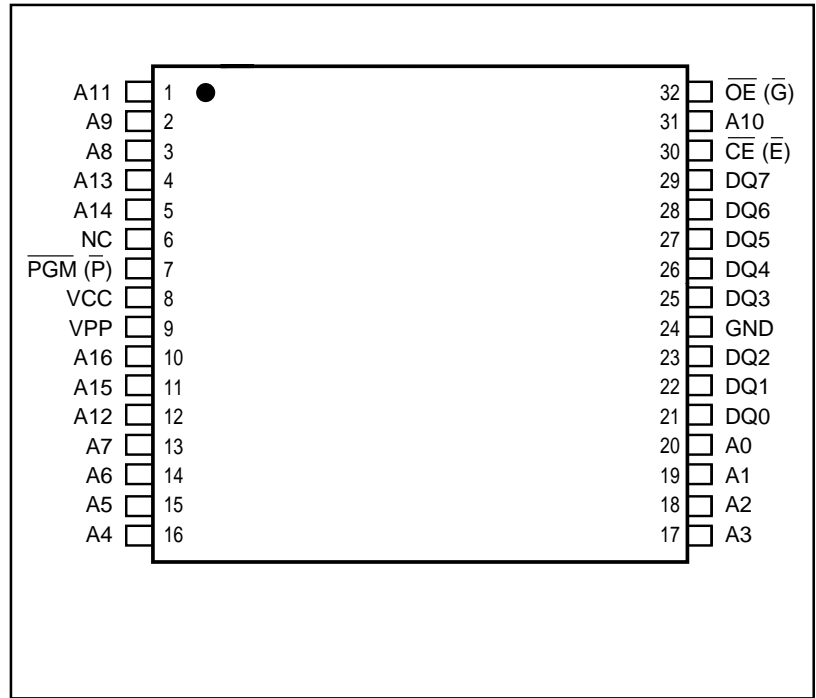
**PIN DESCRIPTIONS**

A0-A16	Address Inputs
$\overline{CE}$ ( $\overline{E}$ )	Chip Enable Input
DQ0-DQ7	Data Inputs/Outputs
$\overline{OE}$ ( $\overline{G}$ )	Output Enable Input
$\overline{PGM}$ ( $\overline{P}$ )	Program Enable Input
Vcc	Power Supply Voltage
VPP	Program Supply Voltage
GND	Ground
NC	No Internal Connection

**32-Pin PLCC**



**32-Pin TSOP**



## FUNCTIONAL DESCRIPTION

Upon delivery, the MM27C010 has 1,048,576 bits in the "ONE", or HIGH state. "ZEROS" are loaded into the MM27C010 through the procedure of programming.

The programming mode is entered when  $V_{PP} \pm 0.25V$  is applied to the  $V_{PP}$  pin,  $\overline{CE}$  and  $\overline{PGM}$  is at  $V_L$ , and  $\overline{OE}$  is at  $V_{IH}$ . For programming, the data to be programmed is applied eight bits in parallel to the data output pins.

The write programming algorithm reduces programming time by using 100  $\mu s$  programming pulses followed by a byte verification to determine whether the byte has been successfully programmed. If the data does not verify, an additional pulse is applied for a maximum of 25 pulses. This process is repeated while sequencing through each address of the EPROM.

The write programming algorithm programs and verifies at  $V_{CC} = 6V$  and  $V_{PP} = 12.5V$ . After the final address is completed, all byte are compared to the original data with  $V_{CC} = 5.25V$ .

### Program Inhibit

Programming of multiple MM27C010s in parallel with different data is also easily accomplished. Except for  $\overline{CE}$ , all like inputs of the parallel MM27C010 may be common. A TTL low-level program pulse applied to an MY27B01  $\overline{CE}$  input with  $V_{PP} = 12.5 \pm 0.25V$ ,  $\overline{PGM}$  LOW and  $\overline{OE}$  HIGH will program that MM27C010. A high-level  $\overline{CE}$  input inhibits the other MM27C010 from being programmed.

### Program Verify

A verify should be performed on the programmed bits to determine that they were correctly programmed. The verify should be performed with  $\overline{OE}$  and  $\overline{CE}$  at  $V_L$ ,  $\overline{PGM}$  at  $V_{IH}$ , and  $V_{PP}$  between 12.25V and 12.75V.

### Auto Select Mode

The auto select mode allows the reading out of a binary code from an EPROM that will identify its manufacturer and type. This mode is intended for use by programming equipment for the purpose of automatically matching the device to be programmed with its corresponding programming algorithm. This mode is functional in the  $2 \text{ } ^\circ\text{C} \pm 5^\circ\text{C}$  ambient temperature range that is required when programming the MM27C010.

To activate this mode, the programming equipment must force  $12.0 \pm 0.5V$  on address line A9 of the MY27B010. Two identifier bytes may then be sequenced from the device outputs by toggling address line A0 from  $V_L$  to  $V_{IH}$ . All other address lines must be held at  $V_L$  during auto select mode.

Byte 0 ( $A0 = V_{IL}$ ) represents the manufacturer code, and byte 1 ( $A0 = V_{IH}$ ), the device identifier code. For the MM27B010, these two identifier bytes are given in the Mode Select table. All identifiers manufacturer and device codes will possess odd parity, with the MSB (DQ7) defined as the parity bit.

### Read Mode

The MM27C010 has two control functions, both of which must be logically satisfied in order to obtain data at the outputs. Chip Enable ( $\overline{CE}$ ) is the power control and should be used for device selection. Assuming that addresses are stable, address access time ( $t_{AC}$ ) is equal to the delay from  $\overline{CE}$  to output ( $t_{OE}$ ). Output Enable ( $\overline{OE}$ ) is the output control and should be used to get data to the output pins, independent of device selection. Data is available at the outputs  $t_{OE}$  after the falling edge of  $\overline{OE}$  assuming that  $\overline{CE}$  has been LOW and addresses have been stable for at least  $t_{CC} - t_{DE}$ .

### Standby Mode

The MY27B010 is placed in CMOS standby mode when  $\overline{CE}$  is at  $V_{CC} \pm 0.3V$  and in TTL standby mode when  $\overline{CE}$  is at  $V_{IH}$ . When in standby mode, the outputs are in a high-impedance state, independent of the  $\overline{OE}$  input.

### Output OR-Tieing

To accommodate multiple memory connections, a two-line control function is provided to allow for:

1. Low memory power dissipation, and
2. Assurance that output bus contention will not occur.

It is recommended that  $\overline{CE}$  be decoded and used as the primary device-selecting function, while  $\overline{OE}$  be made a common connection to all devices in the array and connected to the READ line from the system control bus. This assures that all deselected memory devices are in their low-power standby mode and that the output pins are only active when data is desired from a particular memory device.

### System Applications

During the switch between active and standby conditions, transient current peaks are produced on the rising and falling edges of Chip Enable. The magnitude of these transient current peaks is dependent on the output capacitance loading of the device at a minimum, a 0.1  $\mu\text{F}$  ceramic capacitor (high-frequency, low inherent inductance) should be used on each device between  $V_{CC}$  and GND to minimize transient effects. In addition, to overcome the voltage drop caused by the inductive effects of the printed circuit board traces on EPROM arrays, a 4.7  $\mu\text{F}$  bulk electrolytic capacitor should be used between  $V_{CC}$  and GND for each eight devices. The location of the capacitor should be close to where the power supply is connected to the array.

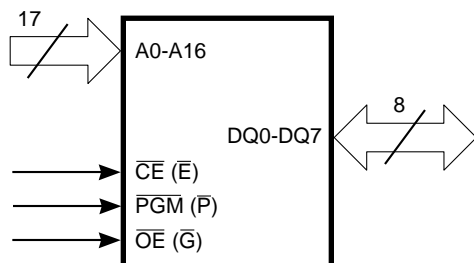
### TRUTH TABLE<sup>(1,2)</sup>

Mode	$\overline{CE}$	$\overline{OE}$	$\overline{PGM}$	A0	A9	$V_{PP}$	Outputs
Read	$V_{IL}$	$V_{IL}$	X	X	X	$V_{CC}$	DOUT
Output Disable	$V_{IL}$	$V_{IH}$	X	X	X	$V_{CC}$	Hi-Z
Standby	$V_{IH}$	X	X	X	X	$V_{CC}$	Hi-Z
Program	$V_{IL}$	$V_{IH}$	$V_{IL}$	X	X	$V_{PP}$	DIN
Program Verify	$V_{IL}$	$V_{IL}$	$V_{IH}$	X	X	$V_{PP}$	DOUT
Program Inhibit	$V_{IH}$	X	X	X	X	$V_{PP}$	Hi-Z
Auto Select <sup>(3)</sup>	Manufacturer Code	$V_{IL}$	X	$V_{IL}$	$V_{H}$	$V_{CC}$	D5H
	Device Code	$V_{IL}$	X	$V_{IH}$	$V_{H}$	$V_{CC}$	0EH

#### Notes:

1.  $V_{H} = 12.0\text{V} \pm 0.5\text{V}$ .
2. X = Either  $V_{IH}$  or  $V_{IL}$ .
3. A1-A8 = A10-A16 =  $V_{IL}$ .
4. See DC Programming Characteristics for  $V_{PP}$  voltage during programming.

### LOGIC SYMBOL



**ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>**

Symbol	Parameter	Value	Unit
V <sub>TERM</sub>	Terminal Voltage with Respect to GND		
	All pins except A9 and V <sub>PP</sub>	-0.6 to V <sub>CC</sub> + 0.5 <sup>(2)</sup>	V
	V <sub>PP</sub>	V <sub>CC</sub> - 0.3 to 13.5 <sup>(2,3)</sup>	V
	A9	-0.6 to 13.5 <sup>(2,3)</sup>	V
	V <sub>CC</sub>	-0.6 to 7.0 <sup>(2)</sup>	V
T <sub>A</sub>	Ambient Temperature with Power Applied	-65 to +125	°C
T <sub>STG</sub>	Storage Temperature (OTP)	-65 to +125	°C
T <sub>STG</sub>	Storage Temperature (All others)	-65 to +150	°C

**Notes:**

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. Minimum DC input voltage is -0.5V. During transitions, inputs may undershoot to -2.0V for periods less than 10 ns. Maximum DC voltage on output pins is V<sub>CC</sub> + 0.5V which may overshoot to V<sub>CC</sub> + 2.0V for periods less than 10 ns.
3. Maximum DC voltage on A9 or V<sub>PP</sub> may overshoot to +13.5V for periods less than 10 ns.

**OPERATING RANGE**

Range	Ambient Temperature	V <sub>CC</sub>
Commercial	0°C to +70°C	5V ± 10%
Industrial <sup>(1)</sup>	-40°C to +85°C	5V ± 10%

**Note:**

1. Operating ranges define those limits between which the functionality of the device is guaranteed.

**DC ELECTRICAL CHARACTERISTICS<sup>(1,2,3)</sup> (Over Operating Range)**

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
V <sub>OH</sub>	Output HIGH Voltage	V <sub>CC</sub> = Min., I <sub>OH</sub> = -400 μA	2.4	—	V
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = Min., I <sub>OL</sub> = 2.1 mA	—	0.45	V
V <sub>IH</sub>	Input HIGH Voltage <sup>(4)</sup>		2.0	V <sub>CC</sub> + 0.5	V
V <sub>IL</sub>	Input LOW Voltage <sup>(4)</sup>		-0.3	0.8	V
I <sub>LI</sub>	Input Load Current	V <sub>IN</sub> = 0V to +V <sub>CC</sub>	—	10	μA
I <sub>LO</sub>	Output Leakage Current	V <sub>OUT</sub> = 0V to +V <sub>CC</sub>	—	10	μA

**Notes:**

1. V<sub>CC</sub> must be applied simultaneously or before V<sub>PP</sub> and removed simultaneously or after V<sub>PP</sub>. Never try to force V<sub>PP</sub> LOW to 1V below V<sub>CC</sub>. Manufacturer suggests to tie V<sub>PP</sub> and V<sub>CC</sub> together during the READ operation.
2. **Caution:** the MM27C010 must not be removed from (or inserted into) a socket when V<sub>CC</sub> or V<sub>PP</sub> is applied.
3. Minimum DC input voltage is -0.5V. During transitions, the inputs may undershoot to -2.0V for periods less than 10 ns. Maximum DC voltage on output pins is V<sub>CC</sub> + 0.5V which may overshoot to V<sub>CC</sub> + 2.0V for periods less than 10 ns.
4. Tested under static DC conditions.

**POWER SUPPLY CHARACTERISTICS<sup>(1,2,5)</sup>** (Over Operating Range)

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
I <sub>CC1</sub>	V <sub>CC</sub> Operating Supply Current <sup>(3)</sup>	V <sub>CC</sub> = Max., $\overline{CE} = V_{IL}$ I <sub>OUT</sub> = 0 mA, f = 5 MHz	Commercial — Industrial	30 40	mA
I <sub>PP1</sub>	V <sub>PP</sub> Current During Read <sup>(4)</sup>	V <sub>CC</sub> = Max., $\overline{CE} = \overline{OE} = V_{IL}$ V <sub>PP</sub> = V <sub>CC</sub>	—	100	μA
I <sub>CCSB0</sub>	V <sub>CC</sub> CMOS Standby Current	$\overline{CE} \geq V_{CC} - 0.3V$	—	50	μA
I <sub>CCSB1</sub>	V <sub>CC</sub> TTL Standby Current	$\overline{CE} \geq V_{IH}$ Other Inputs = V <sub>IH</sub> or V <sub>IL</sub> (TTL Level)	—	1	mA

**Notes:**

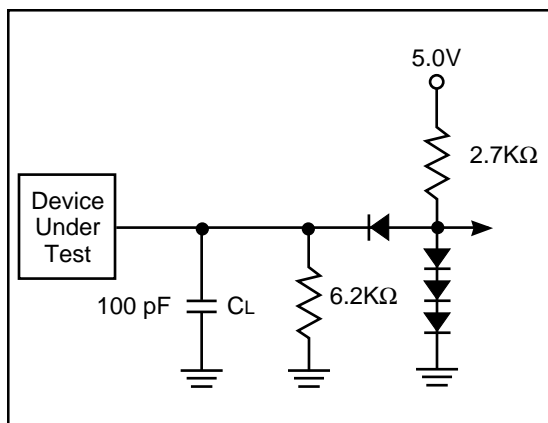
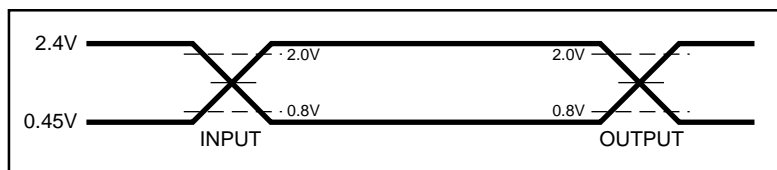
- V<sub>CC</sub> must be applied simultaneously or before V<sub>PP</sub> and removed simultaneously or after V<sub>PP</sub>. Never try to force V<sub>PP</sub> LOW to 1V below V<sub>CC</sub>. Manufacturer suggests to tie V<sub>PP</sub> and V<sub>CC</sub> together during the READ operation.
- Caution:** the MM27C010 must not be removed from (or inserted into) a socket when V<sub>CC</sub> or V<sub>PP</sub> is applied.
- I<sub>CC1</sub> is tested with  $\overline{OE} = V_{IH}$  to simulate open outputs.
- Maximum active power usage is the sum of I<sub>CC</sub> and I<sub>PP</sub>.
- Minimum DC input voltage is -0.5V. During transitions, the inputs may undershoot to -2.0V for periods less than 10 ns. Maximum DC voltage on output pins is V<sub>CC</sub> + 0.5V which may overshoot to V<sub>CC</sub> + 2.0V for periods less than 10 ns.

**CAPACITANCE<sup>(1,2,3)</sup>**

Symbol	Parameter	Conditions	Typ.	Max.	Unit
C <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> = 0V	7	10	pF
C <sub>OUT</sub>	Output Capacitance	V <sub>OUT</sub> = 0V	8	12	pF

**Notes:**

- Typical values are for nominal supply voltage.
- This parameter is only sampled, but not 100% tested.
- Test conditions: T<sub>A</sub> = 25°C, f = 1 MHz.

**SWITCHING TEST CIRCUIT****SWITCHING TEST WAVEFORM****Notes:**

## AC Testing:

- Inputs are driven at 2.4V for a logic "1" and 0.45V for a logic "0".
- Input pulse rise and fall times are < 20 ns.

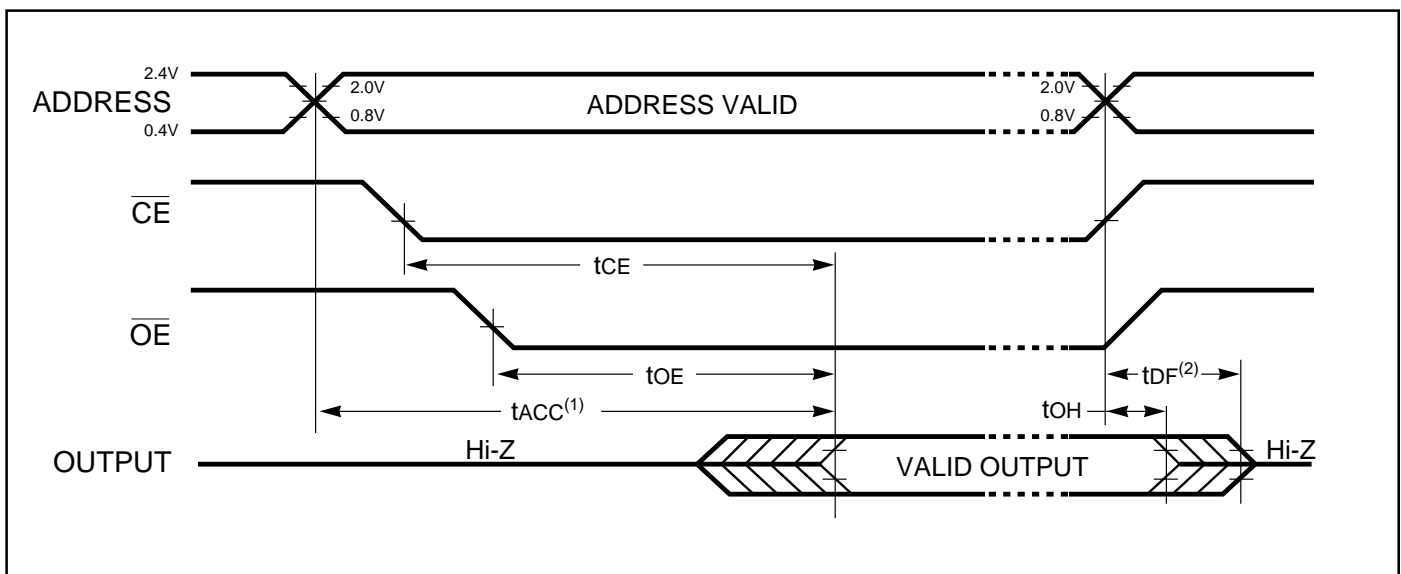
SWITCHING CHARACTERISTICS<sup>(1,2,3,4)</sup> (Over Operating Range)

JEDEC Symbol	Std. Symbol	Parameter	Test Conditions	-90		-12		-15		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	
t <sub>AVQA</sub>	t <sub>ACC</sub>	Address to Output Delay	$\overline{CE} = \overline{OE} = V_{IL}$	—	90	—	120	—	150	ns
t <sub>ELQV</sub>	t <sub>CE</sub>	Chip Enable to Output Delay	$\overline{OE} = V_{IL}$	—	90	—	120	—	150	ns
t <sub>GLQV</sub>	t <sub>OE</sub>	Output Enable to Output Delay	$\overline{CE} = V_{IL}$	—	45	—	50	—	65	ns
t <sub>EHOZ</sub> , t <sub>GHQZ</sub>	t <sub>DF</sub> <sup>(2)</sup>	Chip Enable HIGH or Output Enable HIGH, whichever comes first, to Output Float		—	30	—	35	—	35	ns
t <sub>AVOX</sub>	t <sub>OH</sub>	Output Hold from Address, $\overline{CE}$ or $\overline{OE}$ whichever occurred first		0	—	0	—	0	—	ns

## Notes:

- V<sub>CC</sub> must be applied simultaneously or before V<sub>PP</sub> and removed simultaneously or after V<sub>PP</sub>.
- This parameter is only sampled, not 100% tested.
- Caution:** The MM27C010 must not be removed from (or inserted into) a socket or board when V<sub>PP</sub> or V<sub>CC</sub> applied.
- Output Load: 1 TTL gate and C<sub>L</sub> = 100 pF.  
Input Rise and Fall times: 20 ns.  
Input Pulse Levels: 0.45V to 2.4V.  
Timing Measurement Reference Level: 0.8V to 2V for inputs and outputs.

## SWITCHING WAVEFORMS



## Notes:

- $\overline{OE}$  may be delayed up to  $t_{ACC} - t_{OE}$  after the falling edge of  $\overline{CE}$  without impact on  $t_{ACC}$ .
- $t_{DF}$  is specified from  $\overline{OE}$  or  $\overline{CE}$ , whichever occurs first.

**DC PROGRAMMING CHARACTERISTICS**<sup>(1,2,3,4)</sup> ( $T_A = +25^\circ\text{C} \pm 5^\circ\text{C}$ )

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
V <sub>OH</sub>	Output HIGH Voltage During Verify	I <sub>OH</sub> = -400 $\mu$ A	2.4	—	V
V <sub>OL</sub>	Output LOW Voltage During Verify	I <sub>OL</sub> = 2.1 mA	—	0.45	V
V <sub>IH</sub>	Input HIGH Voltage		2.0	V <sub>CC</sub> + 0.5	V
V <sub>IL</sub>	Input LOW Voltage (All Inputs)		-0.3	0.8	V
V <sub>H</sub>	A9 Auto Select Voltage		11.5	12.5	V
I <sub>LI</sub>	Input Current (All Inputs)	V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub>	—	1	$\mu$ A
I <sub>CC</sub>	V <sub>CC</sub> Supply Current (Program & Verify)		—	50	mA
I <sub>PP</sub>	V <sub>PP</sub> Supply Current	$\overline{\text{CE}} = \text{V}_{\text{IL}}, \overline{\text{OE}} = \text{V}_{\text{IH}}$	—	30	mA
V <sub>CC</sub>	Supply Voltage		5.75	6.25	V
V <sub>PP</sub>	Programming Voltage		12.25	12.75	V

**SWITCH PROGRAMMING CHARACTERISTICS**<sup>(1,2,3,4)</sup> ( $T_A = +25^\circ\text{C} \pm 5^\circ\text{C}$ )

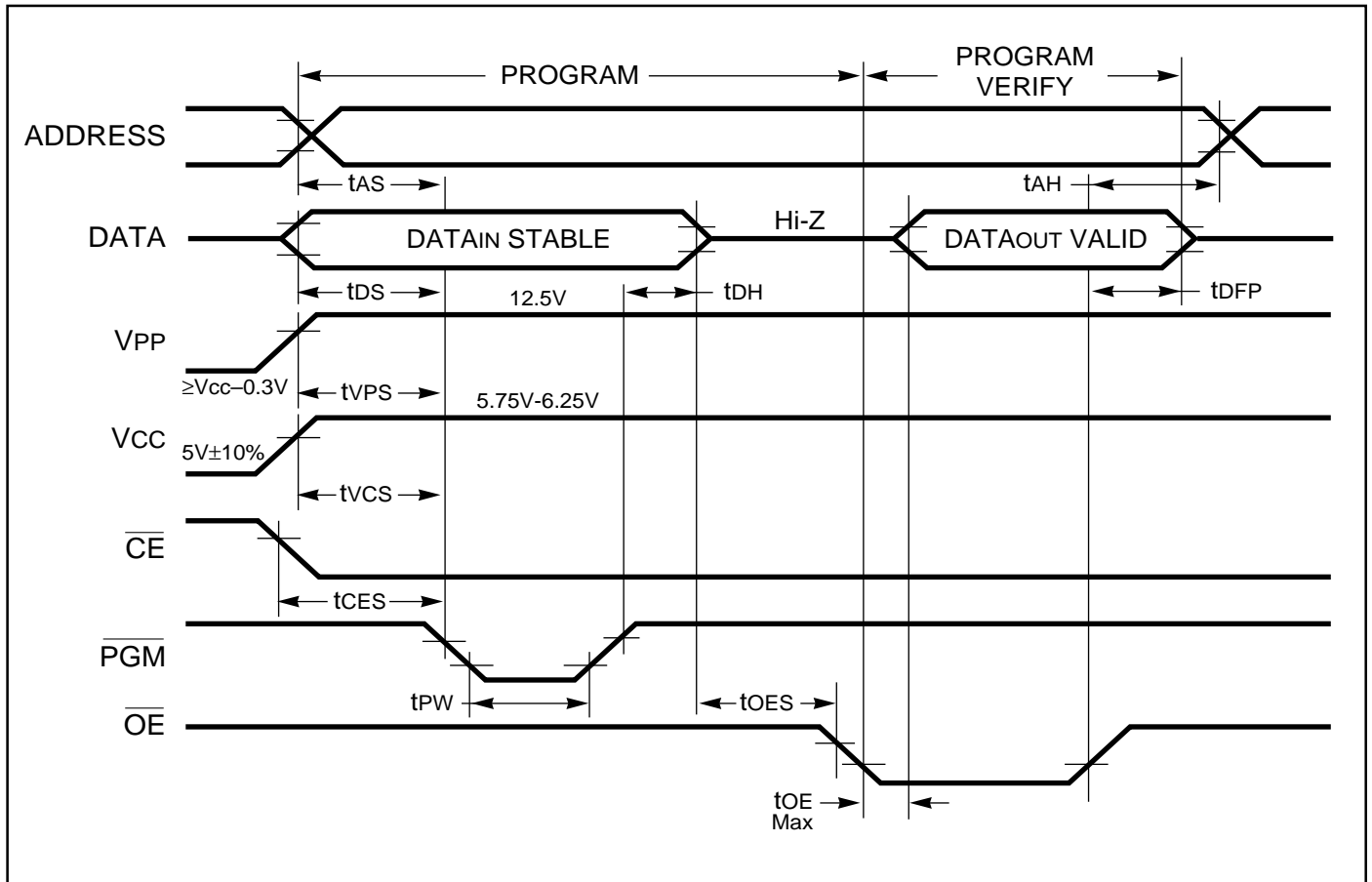
JEDEC Symbol	Std. Symbol	Parameter	Min.	Max.	Unit
t <sub>AVEL</sub>	t <sub>AS</sub>	Address Setup Time	2	—	$\mu$ s
t <sub>DZGL</sub>	t <sub>OES</sub>	$\overline{\text{OE}}$ Setup Time	2	—	$\mu$ s
t <sub>DVEL</sub>	t <sub>DS</sub>	Data Setup Time	2	—	$\mu$ s
t <sub>GHAX</sub>	t <sub>AH</sub>	Address Hold Time	0	—	$\mu$ s
t <sub>EHDX</sub>	t <sub>DH</sub>	Data Hold Time	2	—	$\mu$ s
t <sub>GHQZ</sub>	t <sub>DFP</sub>	$\overline{\text{OE}}$ to Output Float Delay	0	130	ns
t <sub>VPS</sub>	t <sub>VPS</sub>	V <sub>PP</sub> Setup Time	2	—	$\mu$ s
t <sub>ELEH1</sub>	t <sub>PW</sub>	PGM Program Pulse Width	95	105	$\mu$ s
t <sub>VCS</sub>	t <sub>VCS</sub>	V <sub>CC</sub> Setup Time	2	—	$\mu$ s
t <sub>ELPL</sub>	t <sub>CES</sub>	$\overline{\text{CE}}$ Setup Time	2	—	$\mu$ s
t <sub>GLQV</sub>	t <sub>OE</sub>	Data Valid from $\overline{\text{OE}}$	—	150	ns

**Notes:**

- V<sub>CC</sub> must be applied simultaneously or before V<sub>PP</sub> and removed simultaneously or after V<sub>PP</sub>.
- V<sub>PP</sub> must be  $\geq$  V<sub>CC</sub> during the entire programming and verifying procedure.
- When programming MM27C010, a 0.1  $\mu$ F capacitor is required across V<sub>PP</sub> and ground to suppress spurious voltage transients which may damage the device.
- Programming characteristics are sampled but not 100% tested at worst-case conditions.



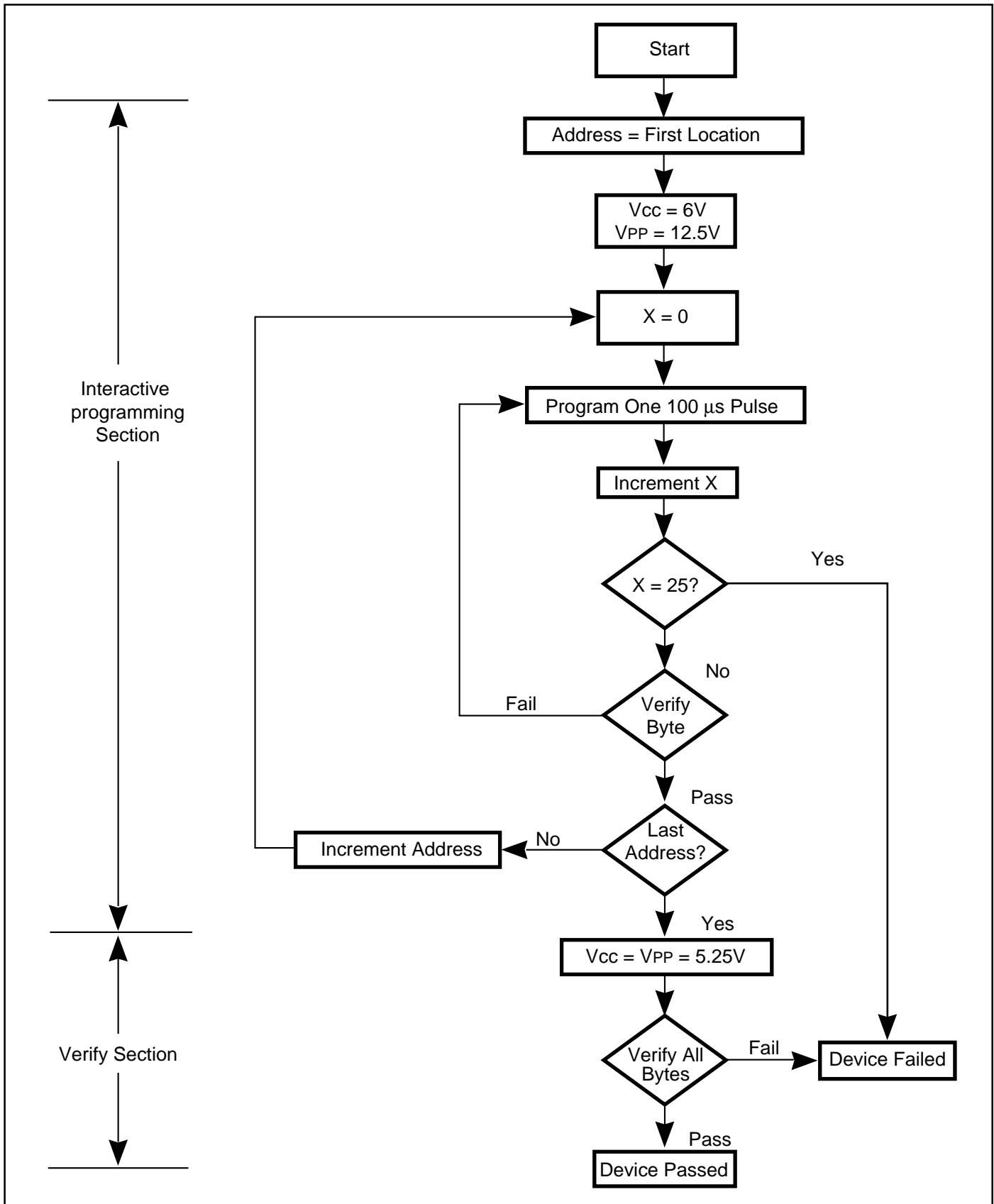
PROGRAMMING ALGORITHM WAVEFORM<sup>(1,2)</sup>



Notes:

1. The timing reference level is 0.8V to 2V for inputs and outputs.
2.  $t_{OE}$  and  $t_{DFP}$  are characteristics of the device but must be accommodated by the programmer.

PROGRAMMING FLOW CHART



**ORDERING INFORMATION****Commerical Range: 0°C to +70°C**

Speed (ns)	Order Part Number	Package
90	MM27C010-90W	600-mil Plastic DIP
	MM27C010-90PL	PLCC – Plastic Leaded Chip Carrier
	MM27C010-90T	TSOP
120	MM27C010-12W	600-mil Plastic DIP
	MM27C010-12PL	PLCC – Plastic Leaded Chip Carrier
	MM27C010-12T	TSOP
150	MM27C010-15W	600-mil Plastic DIP
	MM27C010-15PL	PLCC – Plastic Leaded Chip Carrier
	MM27C010-15T	TSOP

**ORDERING INFORMATION****Industrial Range: –40°C to +85°C**

Speed (ns)	Order Part Number	Package
90	MM27C010-90PLI	PLCC – Plastic Leaded Chip Carrier
	MM27C010-90TI	TSOP
120	MM27C010-12PLI	PLCC – Plastic Leaded Chip Carrier
	MM27C010-12TI	TSOP
150	MM27C010-15PLI	PLCC – Plastic Leaded Chip Carrier
	MM27C010-15TI	TSOP